

IN THE SPECIFICATION

Please replace the paragraph beginning at page 4, line 24, with the following rewritten paragraph:

[0027] In the thermoelectric module 4, the heat-radiation side insulating substrate 4a is opposite to a heat-absorption side insulating substrate 4b to constitute a pair. On an upper surface of the heat-radiation side insulating substrate 4a and a lower surface of the heat-absorption side insulating substrate 4b, there are formed first lower electrodes 4c and second upper electrodes 4d, respectively. As a raw material of the heat-radiation side insulating substrate 4a and the heat-absorption side insulating substrate 4b, Al_2O_3 or AlN is selected. The first lower electrodes ~~4a~~ 4c and the second upper electrodes 4d connect a plurality of N-type and P-type semiconductor tips in series such that the N-type and P-type semiconductor chips are alternately arranged: N-P-N-P----- . One of the first lower electrodes 4c to which one of the N-type semiconductor chips is connected which is located at an outermost ~~positioned~~ position is connected with a lead wire, while one of the second upper electrodes 4d to which one of the P-type semiconductor chips is connected which is located at another outermost position is connected with another lead wire.

[0030] In this semiconductor laser module, the case 1 is formed of a fernico family alloy which has a small thermal expansion rate relative to the glass plate 10 and each of the ceramic substrates 4a and 4b. As examples of such as an alloy, an alloy comprising 54 weight % Fe, 29 weight % Ni, and 17% Co, and an alloy comprising 58 weight % Fe and 42% Ni. The thermoelectric module 4 is adhered to a bottom inside surface of the case 1 via the soldering agent layer ~~6a~~ 5a, as previously described.

[0031] A heat-absorption side second soldering layer 15a is provided between an upper end of the N-type semiconductor chip 4e (an upper end of the P-type semiconductor chip 4f) and the heat-absorption side insulating electrode ~~4b~~ 4d, while a heat-radiation side second soldering layer 15b is provided between a lower end of the N-type semiconductor

chip 4e (a lower end of the P-type semiconductor chip 4f) and the heat-radiation side insulating electrode 4a 4c.

[0032] In summary, the case 1 and heat-radiation side insulating substrate 4a are soldered to each other by way of the first soldering layer 5a formed of a first soldering agent. The upper end of the P-type (N-type) semiconductor chip and the heat-absorption side insulating substrate 4b are soldered to each other by way of the heat-absorption side soldering layer ~~15b~~ 15a which is formed of a second soldering agent of 95Sn5Sb (melting point: 232° Centigrade/Liquidus). The lower end of the P-type (N-type) semiconductor chip and the heat-radiation side insulating substrate 4a are soldered to each other by way of the heat-radiation side soldering layer ~~15a~~ 15b. The first soldering agent and the second soldering agent are identical in raw material.